

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Original): A semiconductor device, comprising:
 - a SOI wafer having a stacked structure of a first silicon layer, a buried insulating film and a second silicon layer;
 - a trench formed by removing a predetermined region of the second silicon layer;
 - a first silicide layer formed at side walls of the trench;
 - a device isolation film defining an active region of the SOI wafer formed by filling the trench;
 - a gate electrode having a gate insulation film formed on the active region of the SOI wafer;
 - an insulation spacer formed at side walls of the gate electrode;
 - impurity junction regions formed at both sides of the gate electrode in the active region of the SOI wafer; and
 - a second silicide layer formed on the gate electrode and the impurity regions.
2. (Original): The semiconductor device according to claim 1, wherein the first and the second silicide layers comprise a metal selected from the group consisting of titanium, cobalt, nickel, and tungsten.

Claims 3-9. (Canceled):